

This diagram shows a cross-sectional view of a semiconductor device. A gate stack, labeled 180, is positioned on a substrate 102. The gate stack includes a gate dielectric layer 270 and a gate electrode layer 260. On either side of the gate stack, there are spacers 128a and 128b. The spacers 128a and 128b are formed on a surface 106. The spacers 128a and 128b are separated by a gap 140. The spacers 128a and 128b are formed on a surface 106. The spacers 128a and 128b are separated by a gap 140. The spacers 128a and 128b are formed on a surface 106. The spacers 128a and 128b are separated by a gap 140.